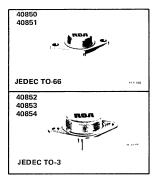


Power Transistors

40850 40851 40852 40853 40854



450-V Silicon N-P-N Types

For Off-Line Switching-Regulator Type Power-Supply Applications

Features:

- High-voltage ratings for operation from power lines without a step-down transformer
- □ Popular JEDEC TO-3 and TO-66 hermetic packages

Applications:

- For use in switching-regulator supplies which feature:
 - A substantial reduction in size and weight due to elimination of the 60-Hz power transformer.
- Operation with a substantial reduction of heat

RCA 40850–40854, inclusive, are silicon n-p-n power transistors, selected from RCA's line of silicon power transistors, for power-supply applications. Their high-voltage ratings (450 V) permit operation directly off the power line thereby eliminating the heavy and bulky 60-Hz power transformer.

Their fast switching speeds (t_r plus t_f equal to less than 2.0 μ s) permit operation above the audio-frequency range (20 to 30 kHz) for quiet performance, and permit the use of small ferrite-core transformers for changing the voltage level.

These types have sufficient voltage capability to be used as push-pull inverters or pulse-width-modulated inverters operating directly off the 120-V power line.

- **a** 5-V, off-line supplies with current ratings of 25, 50, 100, or 200 A
- 30-V, off-line supplies with current ratings of 5, 10, 20, or 40 A

Types 40850-40854 have sufficient voltage capability to operate as switching regulators off a 240-V line; for 120-V lines, the prototypes can be used.

A brief description of these types, together with prototype identification, is given in the tables on pages 2, 3, and 4.

MAXIMUM RATINGS, Absolute-Maximum Values:

	40850	40851	40852 th	40853	40854	
COLLECTOR-TO-BASE VOLTAGE,						
VCBO COLLECTOR-TO-EMITTER	450	450	450	450	450 -	V
SUSTAINING VOLTAGE:						
With base open, VCEO(sus)	300	350	350	300	300	V
With external base-to-emitter						
resistance (RBE) \leq 50 Ω ,						
VCER(sus)	400	375	375	375	325	V
EMITTER-TO-BASE VOLTAGE,						
V _{EBO}	6	9	9	6	6	V
COLLECTOR CURRENT, IC						
Continuous and Average	2	7	7	10	15	Α
Peak (10 ms max.)	5	10	10	15	30	Α
CONTINUOUS BASE CURRENT, IB	1	4	4	5	10	Α

Formerly RCA-40832.

Continued on following page.

MAXIMUM RATINGS (cont'd):	40850	40851	40852 ■	40853	40854	
TRANSISTOR DISSIPATION, PT:						
(Power Dissipation-Limited Region*)						
At case temperaures up to 25°C	35	45	100	100	175	W
At case temperaures above 25°C		See deratir	g curves in proto	otype bulletin:	S.	
and in the IS/b-Limited Region*						
TEMPERATURE RANGE:						
Storage & Operating (Junction)	4			°C		-
PIN TEMPERATURE (During						
Soldering):						
At distances ≥1/32 in.				_		
(0.8 mm) from case for 10 s max.	-		23	о _о с ———		-

^{*} Safe-operating-area curves for prototype devices should be extended to the maximum values of collector current given for these devices.

TERMINAL CONNECTIONS (All Types)

Pin 1 - Base

Pin 2 - Emitter

Mounting Flange, Case - Collector

Type 40850 (For 5-V, 25-A & 30-V, 5-A Power Supplies)

Package: JEDEC TO-66

Application Information: See "RCA Power Circuits" manual SP-52 and RCA Application Note AN3065

ELECTRICAL CHARACTERISTICS, At Case Temperature (T_C) = 25°C Unless Otherwise Specified

CHARACTERISTIC	SYMBOL TEST CONDITIONS	LIMITS		LINUTO	
		MIN.	MAX.	UNITS	
Collector-Cutoff Current:	ICEV	V _{CE} = 450 V, V _{BE} = -1.5 V	_	0.2	mA
With base reverse biased	ICEV	$V_{CE} = 450 \text{ V}, V_{BE} = -1.5 \text{ V}, T_{C} = 125^{\circ}\text{C}$	_	2	mA
Collector-to-Emitter Voltage With base open	VCEO ^a	I _C = 0.2 A, I _B = 0	300		V
Collector-to-Emitter Voltage With external base-to- emitter resistance (RBE)	V _{CER} ^a	I _C = 0.2 A, R _{BE} = 50 Ω	400	_	V
Emitter-to-Base Voltage	VEBO	I _E = 5 mA, I _C = 0	6	_	V
DC Forward-Current Transfer Ratio	hFE	I _C = 0.75 A, V _{CE} = 10 V	25	_	
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	I _C = 2 A, I _B = 0.4 A	-	2.0	V
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	I _C = 2 A, I _B = 0.4 A	_	2.0	V
Second-Breakdown Collector Current: With base forward biased	l _{S/b} a	V _{CE} = 100 V	0.35	_	А
Second-Breakdown Energy: With base reversed biased	E _{S/b} a	L = 100 μH, I _C (PEAK) = 2 A, R = 20 Ω V _{BE} = -4 V	0.2	_	mJ

a For characteristics curves and test conditions, refer to published data for prototype 2N3585 (File 138).

Formerly RCA-40832

Type 40851 (For 5-V, 50-A & 30-V, 10-A Power Supplies)

Package: JEDEC TO-66

Applications Information: See "RCA Power Circuits" manual SP-52 and RCA Application Note AN4509

ELECTRICAL CHARACTERISTICS, At Case Temperature (T_C) = 25°C Unless Otherwise Specified

CHARACTERISTIC	SYMBOL TEST CONDITIONS	LIMITS		1	
CHARACTERISTIC	STIVIBUL	TEST CONDITIONS	MIN.	MAX.	UNITS
Collector-Cutoff Current:	ICEV	$V_{CE} = 450 \text{ V}, V_{BE} = -1.5 \text{ V}$	-	0.5	mA
With base reverse biased	ICEV	$V_{CE} = 450 \text{ V}, V_{BE} = -1.5 \text{ V}, T_{C} = 125^{\circ}\text{C}$		5	mA
Collector-to-Emitter Voltage With base open	V _{CEO} ^a	I _C = 0.2 A, I _B = 0	350	_	٧
Collector-to-Emitter Voltage With external base-to- emitter resistance (RBE)	V _{CER} ^a	I_{C} = 0.2 A, R_{BE} = 50 Ω	375	-	v
Emitter-to-Base Voltage	V _{EBO}	I _E = 1 mA, I _C = 0	9		V
DC Forward-Current Transfer Ratio	pEE	I _C = 1.2 A, V _{CE} = 1.0 V	12	-	
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	I _C = 4 A, I _B = 0.8 A	-	3	٧
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	I _C = 4 A, I _B = 0.8 A	_	2	٧
Second-Breakdown Collector Current: With base forward biased	I _{S/b} ^a	V _{CE} = 50 V	0.9	_	А
Second-Breakdown Energy: With base reversed biased	E _{S/b}	L = 100 μH, $I_C(PEAK)$ = 3 A, R = 50 Ω V_{BE} = -4 V	0.45	_	mJ

^a For characteristics curves and test conditions, refer to published data for prototype 2N6079 (File 492).

Type 40852 (For 5-V, 50-A & 30-V, 10-A Power Supplies)

Package: JEDEC TO 3

Applications Information: See "RCA Power Circuits" manual SP-52 and RCA Application Note AN4509

ELECTRICAL CHARACTERISTICS, At Case Temperature (TC) = 25°C Unless Otherwise Specified.

CHARACTERISTIC	SYMBOL	TEST CONDITIONS	LIMITS		LINUTO
	STIVIBUL	TEST CONDITIONS	MIN.	MAX.	UNITS
Collector-Cutoff Current:	ICEV	V _{CE} = 450 V, V _{BE} = -1.5 V	-	0.5	mA
With base reverse biased	ICEV	$V_{CE} = 450 \text{ V}, V_{BE} = -1.5 \text{ V}, T_{C} = 125^{\circ}\text{C}$	T -	- 5	mA
Collector-to-Emitter Voltage With base open	V _{CEO} ^a	I _C = 0.2 A, I _B = 0	350	·-	V
Collector-to-Emitter Voltage With external base-to- emitter resistance (RBE)	V _{CER} ª	I _C = 0.2 A, R _{BE} = 50 Ω	375	-	V
Emitter-to-Base Voltage	VEBO	IE = 1 mA, IC = 0	9	-	V
DC Forward-Current Transfer Ratio	hFE	I _C = 1.2 A, V _{CE} = 1.0 V	12	-	
Collector-to-Emitter Saturation Voltage	VCE (sat)	I _C = 4 A, I _B = 0.8 A	-	3.0	V
Base-to-Emitter Saturation Voltage	VBE(sat)	I _C = 4 A, I _B = 0.8 A	-	2.0	V
Second-Breakdown Collector Current: With base forward biased	IS/b	V _{CE} = 40 V	2.5	-	А
Second-Breakdown Energy: With base reversed biased	E _{S/b} ^a	L = 100 μH, $I_C(PEAK)$ = 3 A, R = 50 Ω V_{BE} = -4 V	0.45	_	mJ

^a For characteristics curves and test conditions, refer to published data for prototype 2N5840 (File 410).

Type 40853 (For 5-V, 100-A & 30-V, 20-A Power Supplies)

Package: JEDEC TO-3

Applications Information: See "RCA Power Circuits" manual SP-52

ELECTRICAL CHARACTERISTICS, At Case Temperature (7C) = 25°C Unless Otherwise Specified

CHARACTERISTIC	SYMBOL TEST CONDITIONS	LIMITS		UNITS	
		MIN.	MAX.	0.4113	
Collector-Cutoff Current:	ICEV	V _{CE} = 450 V, V _{BE} = -1.5 V	- '	1.0	mA
With base reverse biased	ICEV	V _{CE} = 450 V, V _{BE} = -1.5 V, T _C = 125 OC	-	10	mA
Collector-to-Emitter Voltage With base open	V _{CEO} ^a	I _C = 0.2 A, I _B = 0	300	-	٧
Collector-to-Emitter Voltage With external base-to- emitter resistance (RBE)	V _{CER} ^a	I _C = 0.2 A, R _{BE} = 50 Ω	375	-	٧
Emitter-to-Base Voltage	VEBO	IE = 5 mA, IC = 0	6	-	V
DC Forward-Current Transfer Ratio	hFE	I _C = 5 A, V _{CE} = 4 V	10	-	
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	I _C = 8 A, I _B = 1.6 A	-	3.0	v
Base-to-Emitter Saturation Voltage	VBE(sat)	IC = 8 A, IB = 1.6A	_	2.0	٧
Second-Breakdown Collector Current: With base forward biased	I _{S/b} a	V _{CE} = 50 V	2.2	_	А
Second-Breakdown Energy: With base reversed biased	E _{S/b}	L = 50 μ H, I _C (PEAK) = 5 A, R = 20 Ω V _{BE} = -4 V	0.62	-	mJ

^a For characteristics curves and test conditions, refer to published data for prototype 2N5805 (File 407).

Type 40854 (For 5-V, 200-A & 30-V, 40-A Power Supplies)

Package: JEDEC TO-3

Applications Information: See "RCA Power Circuits" manual SP-52

ELECTRICAL CHARACTERISTICS, At Case Temperature (T_C) = 25^oC Unless Otherwise Specified.

CHARACTERISTIC	SYMBOL TEST CONDITIONS	LIMITS		UNITS	
		MIN.	MAX.	5.4113	
Collector-Cutoff Current:	ICEV	V _{CE} = 450 V, V _{BE} = -1.5 V		1.0	mA
With base reverse biased	ICEV	V _{CE} = 450 V, V _{BE} = -1.5 V, T _C = 125 ^o C	-	10	mA
Collector-to-Emitter Voltage With base open	V _{CEO} ^a	I _C = 0.2 A, I _B = 0	300	_	٧
Collector-to-Emitter Voltage With external base-to- emitter resistance (RBE)	V _{CER} ^a	I _C = 0.2 A, R _{BE} = 50 Ω	325	_	V
Emitter-to-Base Voltage	VEBO	I _E = 5 mA, I _C = 0	6	_	V
DC Forward-Current Transfer Ratio	hFE	I _C = 10 A, V _{CE} = 4 V	8	_	
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	I _C = 16 A, I _B = 3.2 A	-	3.0	٧
Base-to-Emitter Saturation Voltage	VBE(sat)	I _C = 16 A, I _B = 3.2 A	-	3.0	V
Second-Breakdown Collector Current: With base forward biased	I _{S/b} ^a	VCE = 30 V	5.8	-	А
Second-Breakdown Energy: With base reversed biased	E _{S/b} ^a	L = 50 μH, $I_C(PEAK)$ = 10 A, R = 50 Ω V _{BE} = -4 V	2.5	-	mJ

a For characteristics curves and test conditions, refer to published data for prototype 2N6251 (File 523).